

# NCE P-Channel Enhancement Mode Power MOSFET

### Description

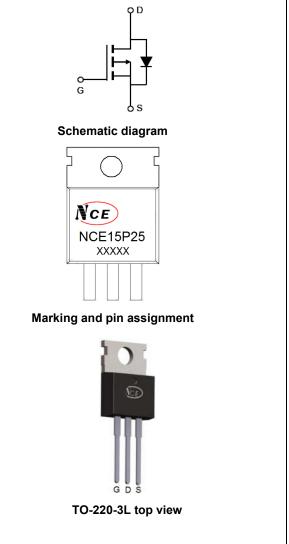
The NCE15P25 uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

#### **General Features**

- V<sub>DS</sub> =-150V,I<sub>D</sub> =-25A
  R<sub>DS(ON)</sub> <140mΩ @ V<sub>GS</sub>=-10V
- Super high dense cell design
- Advanced trench process technology
- Reliable and rugged
- High density cell design for ultra low On-Resistance

### Application

• Portable equipment and battery powered systems



### 100% UIS TESTED!

**100% ΔVds TESTED!** 

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE15P25	NCE15P25	TO-220-3L	-	-	-

#### Absolute Maximum Ratings (T<sub>c</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	-150	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	Ι <sub>D</sub>	-25	А
Drain Current-Continuous(T <sub>C</sub> =100℃)	I <sub>D</sub> (100℃)	-17	A
Pulsed Drain Current	I <sub>DM</sub>	-100	A
Maximum Power Dissipation	PD	120	W
Derating factor		0.8	W/℃
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 To 175	°C



#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case (Note 2)R1.25
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### Electrical Characteristics (T<sub>c</sub>=25<sup>°</sup>C unless otherwise noted)

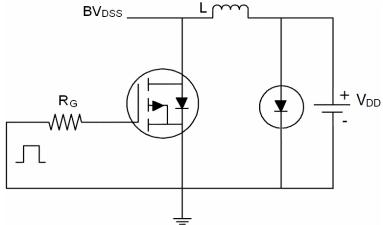
Parameter	Symbol	Condition	on Min		Мах	Unit
Off Characteristics			•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250µA	-150	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-150V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)			•			I.
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250µA	-1.5	-2	-3	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A	-		140	mΩ
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =-5V,I <sub>D</sub> =-20A	5	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>		-	7650	-	pF
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =-75V, $V_{GS}$ =0V,	-	148	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	131	-	pF
Switching Characteristics (Note 4)						L.
Turn-on Delay Time	t <sub>d(on)</sub>		-	17	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =-75V,I <sub>D</sub> =-20A	-	80	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	V <sub>GS</sub> =-10V,R <sub>GEN</sub> =9.1Ω	-	45	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	65	-	nS
Total Gate Charge	Qg	N/ 75)// 00A	-	137	-	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =-75V,I <sub>D</sub> =-20A,	-	25	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =-10V	-	28	-	nC
Drain-Source Diode Characteristics						I
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-25A	-	-	-1.2	V
Diode Forward Current (Note 2)	Is	-	-	-	-25	А
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF =-25A	-	90	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	105	-	nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

#### Notes:

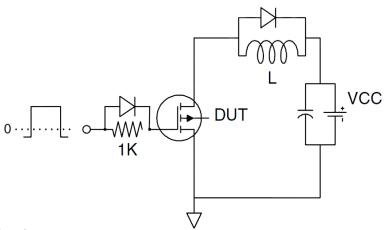
- **1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition: Tj=25 $^\circ\!\!\mathbb{C}$ ,V\_DD=-50V,V\_G=-10V,L=0.5mH,Rg=25 $\Omega$



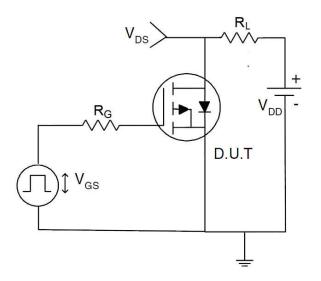
# Test Circuit 1) E<sub>AS</sub> Test Circuit



# 2) Gate Charge Test Circuit

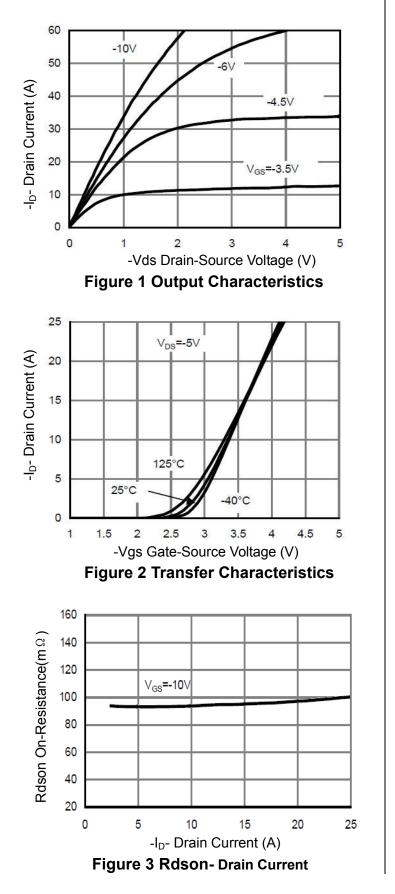


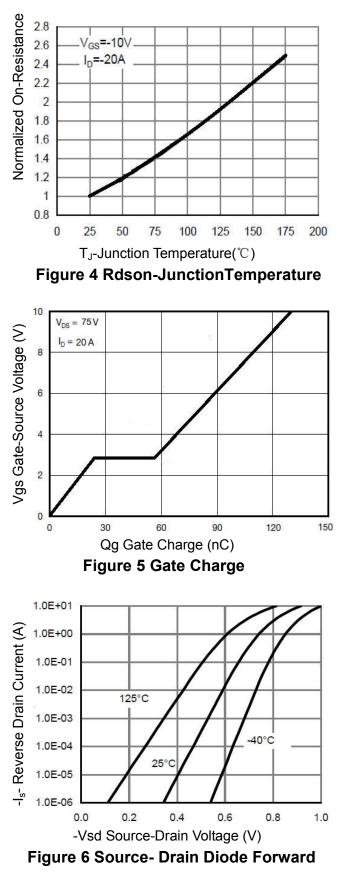
3) Switch Time Test Circuit





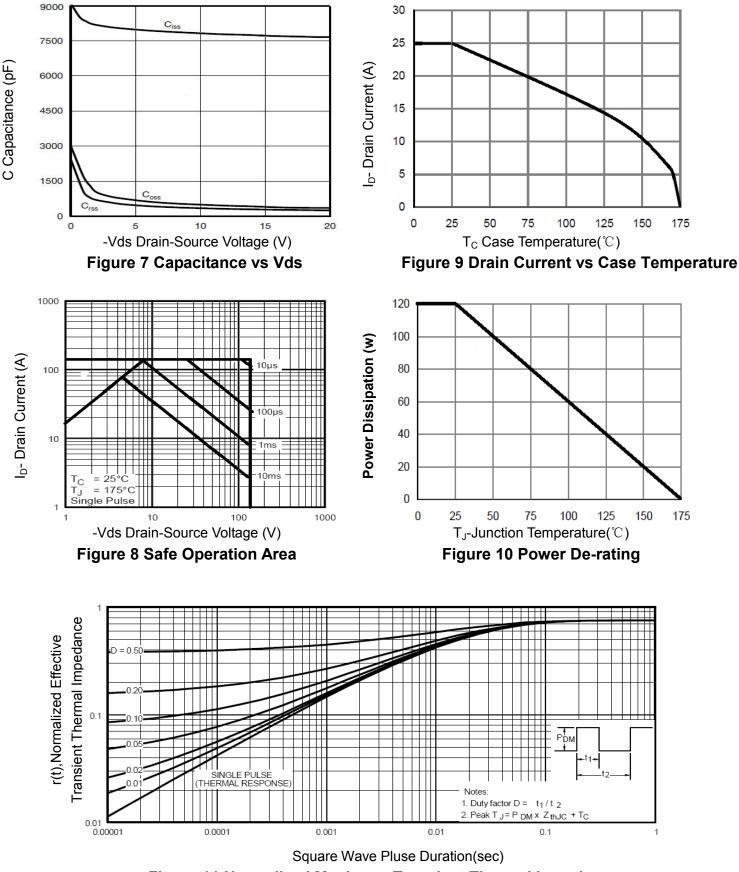
## **Typical Electrical and Thermal Characteristics (Curves)**







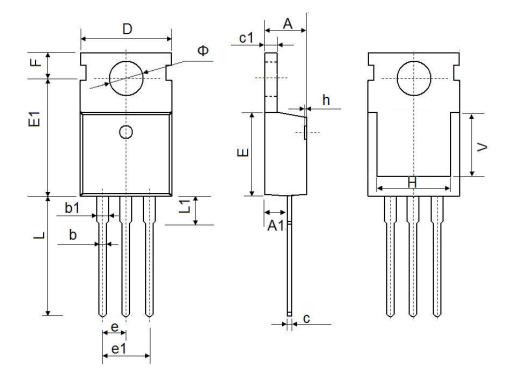
http://www.ncepower.com







# TO-220-3L Package Information



	Dimensions	In Millimeters	Dimensions In Inches	
Symbol	Min.	Max.	Min.	Max.
А	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
С	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
е	2.540 TYP.		0.100 TYP.	
e1	4.980 5.180		0.196	0.204
F	2.650	2.950	0.104	0.116
Н	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150



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